ION SOURCE DEVICE

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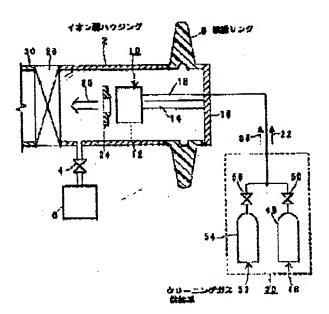
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Abstract of JP2000323051

PROBLEM TO BE SOLVED: To easily eliminate contamination on an inner surface of an insulating ring of the like mounted on an ion source housing. SOLUTION: This ion source device holds an ion source head 10 having a plasma generating part 12 through an insulating ring 8 in an ion source housing 2 which is vacuum-exhausted, and is provided with a cleaning gas supply system 52 for supplying cleaning gas 58 containing halogen gas into the ion source housing 2.



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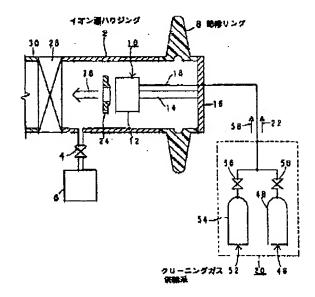
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(54)【発明の名称】 イオン都装置

(57)【要約】

【課題】 イオン扱ハウジングに取り付けられた絶縁リングの内面等の汚れを簡単に除去することができるようにする。

【解決手段】 このイオン源装置は、真空排気されるイオン源ハウジング2内に、絶縁リング8を介して、プラズで生成部12を有するイオン源へッド10を保持した構造をしている。更に、イオン源ハウジング2内にハロゲンガスを含むクリーニングガス58を供給するクリーニングガス供給系52を備えている。



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【特許請求の範囲】

【請求項1】 真空排気されるイオン源ハウジング内に、絶縁リングを介して、プラズマ生成部を有するイオン線ヘッドを保持した構造のイオン源装置において、前記イオン源ハウジング内にハロゲンガスを含むクリーニングガスを供給するクリーニングガス供給系を備えることを特徴とするイオン源装置。

【発明の詳細な説明】

[0001]

【発明の属する技術分野】この発明は、例えばイオン注入装置等に用いられるものであって、イオン源ハウジング内に、絶縁リングを介して、プラズマ生成部を有するイオン源へッドを保持した構造のイオン源装置に関し、より具体的には、上記絶縁リングの内面等の汚れを簡単に除去する手段に関する。

[0002]

【従来の技術】この種のイオン源装置の従来例を図3に示す。このイオン源装置は、間状のイオン源ハウシング2内に、その一端部に取り付けられた絶縁リング8を介して、アラスマ生成部12を有するイオン源へッド10を保持した構造をしている、イオン源へッド10は、この例では、アラズマ生成部12を支持する支持体14およびこの支持体14を支持する階板16を更に有している。端板16は、絶縁リング8の外端部に取り付けられている。

【0003】アラズマ生成部12には、ガス供給部20からガス導入管18を経由してイオン邸ガス22が導入される。アラズマ生成部12は、詳細は後述するけれども、このイオン郷ガス22を放電分解してアラズマ36(図4参照)を生成する、イオン源ガス22は、例えば、BF3、AsH3、PH3等のように、B、As、P等のドーバント(半導体への注入不純物)を含有するガスである。

【0004】イオン源ハウジング2内であってプラズマ 生成部12の前方近傍には、プラズマ生成部12内で生 成されたプラズマからイオンビーム26を引き出す引出 し電極24が配置されている。この引出し電極24は、 図示しない支持体によって、かつ必要な絶縁を確保し て、イオン源ハウジング2から支持されている。

【0005】上記プラズマ生成部12、支持体14および端板16には、イオンビーム26を所定のエネルギーに加速して引き出すために、図示しない直流電源から、正の高電圧(例えば20~50kV程度)が印加される。上記絶縁リング8は、この高電圧の電気絶縁を保つためのものである。プラズマ生成部12につながるガス導入で18およびガス供給部20にも、通常は上記高電圧が印加される。従ってこれらも通常は高電位にある。【0006】上記イオン源ハウジング2内は、イオンビーム26の損失を少なくする等のために、弁4を介して、真空排気装置6によって所定の高真空(例えば10

-5~10-6 Torr程度) に真空排気される。このイオン酒ハウシング2の他端部には、この例では、弁28を介して、上記イオンビーム26を所望の場所へ導くビームライン管30が接続されている。

【0007】上記プラズマ生成部12の構造の一例を図4に示す。このプラズマ生成部12は、特開平9-35648号公報に記載されたのと同様のものであり、上記イオン湖ガス22が導入されるプラズマ生成容器32と、その一方側内に設けられたU字状のフィラメント38と、プラズマ生成容器32の他方側内に設けられた反射電極42とを備えている。フィラメント38および反射電極42とプラズマ生成容器32との間は、絶縁体40および44によってそれぞれ電気的に絶縁されている。

【0008】プラズマ生成容器32の前面部には、イオン引出しスリット34が設けられている。プラズマ生成容器32内には、図示しない磁界発生手段によって、フィラメント38と反射電極42とを結ぶ軸に沿う方向に磁界37が印加される。

【0009】フィラメント38を通電加熱し、それとプラズマ生成容器32との間でアーク放電を生じさせることによって、イオン源ガス22を放電分解してプラズマ36を生成することができる。その際、上記磁界37および反射電極42は、ガスの電離効率を高める働きをする。

[0010]

【発明が解決しようとする課題】上記イオン源装置においては、アラズマ生成部12に導入されたイオン源ガス22の一部が、イオン引出しスリット34を弾してイオン源ハウジング2内に不可避的に漏れ出す。そしてこのイオン源ガス22を構成するB、As、P等を含む導電性の汚れが、イオン源ハウジング2、絶縁リング8等の内面に付着する。

【0011】特に、絶縁リング8の内面に付着した上記 汚れば、絶縁リング8の絶縁不良を覆き起こすので、こ の汚れが進むと、上記プラズマ生成部12等に前述した 所定の高電圧を印加することができなくなり、このイオ ン源装置を運転することができなくなる。

【0012】これを防止するために従来のイオン源装置では、時々、その運転を止めて当該装置を分解して、絶縁リング8の清掃を行う必要があり、非常に多くの手間と時間とを要していた。また、装置の体止時間が長くなり、複動効率が離かった。

【0013】そこでこの発明は、上記のような稽縁リングの内面等の汚れを簡単に除去することができるようにしたイオン凝集置を提供することを主たる目的とする。 【0014】

【課題を解決するための手段】この発明のイオン源装置は、前記イオン源ハウシング内にハロゲンガスを含むクリーニングガスを供給するクリーニングガス供給系を備

(3) UUU-523UD1 (F2UUU-343UD1A)

えることを特徴としている。

【0015】上記構成によれば、イオン源ハウジンク内にクリーニングガスを供給することによって、上記絶縁リングの内面等に付着していた汚れは、ハロゲン化物のガスとなって除去される。除去されたハロゲン化物のガスは、イオン源ハウジング内を裏空排気することに伴って、イオン源ハウジング外に排出される。このようにして、装置を分解せずに簡単に、しかも装置を分解する場合に比べて非常に短時間で、絶縁リングの内面等の汚れを除去することができる。従って、装置の移動効率も向上する。

[0016]

【発明の実施の形態】図1は、この発明に係るイオン源 変置の一例を示す断面図である。図3に示した従来例と 同一または相当する部分には同一符号を付し、以下にお いては当該従来例との相違点を主に説明する。

【0017】このイオン源装置は、前述したイオン源ハウジング2内にハロゲンガスを含むクリーニングガス58を供給するクリーニングガス供給系52を備えている。

【0018】このクリーニングガス供給系52は、この例では、前述したガス供給部20内に設けられていてクリーニングガス58を供給するクリーニングガス源54 および弁56と、このクリーニングガス源54 からのクリーニングガス58をアラズマ生成部12に供給するガス導入管18とを有している。当該ガス供給部20内には、前述したイオン源ガス22を供給するイオン源ガス(最初まび弁50を有するイオン源ガス供給系466設けられている。ガス導入管18は、この例ではイオン源ガス供給系46とクリーニングガス供給系52とで互いに共用している。従ってこの例では、クリーニング時には、ガス導入管18を経由してプラズマ生成部12(より具体的にはその図4に示すプラズマ生成容器3

2) 内にクリーニングガス58が供給され、更にこのブラズマ生成部12 (具体的にはその図4に示すイオン引出しスリット34)を経由してイオン源ハウジング2内にクリーニングガス58が供給される。

【0019】上記クリーニングガス58は、フッ器ガス、塩柔ガス、塩化フッ素ガス、フッ化イオウガスのようなハロゲンガス、または当該ハロゲンガスと他のガス (例えば不活性ガス)との混合ガスである。

【0020】上記イオン源装置の運転方法の一例を説明すると、イオンビーム26を引き出す通常運転時は、弁4を開いて真空排気装置6によってイオン源ハウジング2内を真空排気すると共に、弁56を閉じ升50を開いてイオン源ガスは給系46からアラズマ生成部12にイオン源ガス22を供給して、前述した作用によってイオンビーム26を引き出す、このとき弁28も開いておく、

【0021】イオン源ハウジング2内のクリーニング時

には、弁28、4および50を閉じておき、弁56を開いてクリーニングガス供給系52からブラズマ生成部12およびイオン源ハウジング2内にクリーニングガス58を供給する。これによって、ブラズマ生成部12内およびイオン源ハウジング2内にクリーニングガス58が満たされ、絶縁リング8の内面に付着していた前述したようなB、As、P等による汚れは、ハロゲン化物のガスとなって、例えばガス状のフッ化ホウ素(例えばBF3)、フッ化して(例えばPF3)等となって、絶縁リング8の内面から除去される、従って、絶縁リング8の絶縁性能を回復させることができる。

【0022】同時に、アラズマ生成部12内の前述した 絶縁体40および44(図4参照)に付着していたB. As、P等の汚れも、上記のようなハロゲン化物のガス となって、絶縁体40および44の表面から除去され る。従って、この絶縁体40および44の絶縁性能を回 復させることもできる。

【0023】更に、イオン減ハウジング2の内面に付者 していた上記のような汚れも、上記と同様にして除去さ れる。

【0024】そして一定時間(例えば予め試験によって 定めておいた時間)が経過したら、弁56を閉じ、かつ 弁4を開いて真空排気装置6によってイオン源ハワジン グ2内を排気する。これによって、上記ハロゲン化物の ガスは、イオン源ハウジング2外に排出される。それに 伴ってイオン源ハウジング2内の真空度が向上する。

【0025】イオン源ハウジング2内の真空度が所定のものに (例えば10つ~10-6个orr程度に) 達したら、イオンビーム26の引き出しを再開することができる。

【0026】上記のようにして、このイオン源装置によれば、装置を分解せずに簡単に、しかも装置を分解する場合に比べて非常に短時間で、絶縁リング8の内面の汚れや、プラズマ生成部12を構成する絶縁体40および44の表面の汚れ等を除去することができる。従って、装置の移動効率も向上する。

【0027】なお、図2に示す例のように、上記クリーニングガス供給系52に、更に、弁60およびガス導入管62を設けて、このガス導入管62か6クリーニングガス58を絶縁リング8の内面付近に供給するようにしても良い。そのようにすれば、絶縁リング8の内面にクリーニングガス58を効率良く供給することができるので、絶縁リング8の内面の汚れをより効率良く除去することが可能になる。

[0028]

【発明の効果】以上のようにこの発明によれば、上記のようなクリーニングガス供給系を備えているので、装置を分解せずに簡単に、しかも装置を分解する場合に比べて非常に短時間で、絶縁リングの内面等の汚れを除去す

ることができる。従って、装置の稼動効率も向上する。 【図面の簡単な説明】

【図1】この発明に係るイオン源装置の一例を示す断面 図である。

【図2】この発明に係るイオン源装置の他の例を示す断 面図である。

【図3】従来のイオン源装置の一例を示す断面図であ

【図4】図1ないし図3中のブラズマ生成部周りの詳細 例を示す断面図である。

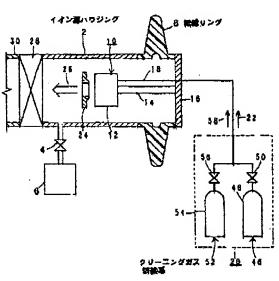
【符号の説明】

2 イオン源ハウジング

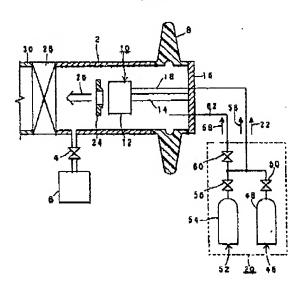
- 6 其空排気装置
- 8 絶縁リング
 - 10 イオン源ヘッド
 - 12 アラスマ生成部
 - 18 ガス導入管
 - 20 ガス供給部
 - 22 イオン源ガス
 - 46 イオン源カス供給系
 - 52 クリーニングガス供給系
 - 58 クリーニングガス

[图1]

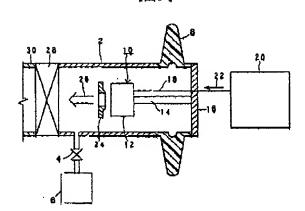




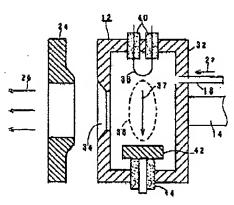
[22]



【図3】



【图4】



CLAIMS

[Claim(s)]

[Claim 1] Ion source equipment characterized by having the cleaning gas supply system which supplies the cleaning gas which contains halogen gas in said ion source housing in ion source housing by which evacuation is carried out in the ion source equipment of the structure which held the ion source head which has the plasma production section through the insulating ring.

[Translation done.]

DETAILED DESCRIPTION

[Detailed Description of the Invention]

[Field of the Invention] This invention is used for ion implantation equipment etc., and, more specifically, relates to a means to remove dirt, such as an inside of the above-mentioned insulating ring, simply, about the ion source equipment of the structure holding the ion source head which has the plasma production section through an insulating ring in ion source housing. [0002]

[Description of the Prior Art] The conventional example of this kind of ion source equipment is shown in drawing 3. This ion source equipment is having structure holding the ion source head 10 which has the plasma production section 12 through the insulating ring 8 attached in the tubed ion source housing 2 at that end section. The ion source head 10 has further the end plate 16 which supports the base material 14 which supports the plasma production section 12, and this base material 14 in this example. The end plate 16 is attached in the heel of an insulating ring 8. [0003] Ion source gas 22 is introduced into the plasma production section 12 via the gas installation tubing 18 from the gas supply section 20. Although the plasma production section 12 is mentioned later for details, discharge decomposition of this ion source gas 22 is carried out, and it generates the plasma 36 (refer to drawing 4). ion source gas 22 — for example, BF3, AsH3, and PH3 etc. — it is gas containing dopants (impregnation impurity to a semi-conductor), such as B, As, and P, like.

[0004] It is in the ion source housing 2, and the cash-drawer electrode 24 which pulls out an ion beam 26 from the plasma generated within the plasma production section 12 is arranged near the front of the plasma production section 12, the base material which does not illustrate this cash-drawer electrode 24 -- and a required insulation is secured and it is supported from the ion source housing 2.

[0005] In order to accelerate and pull out an ion beam 26 to predetermined energy, the forward high voltage (for example, about 20-50kV) is impressed to the above-mentioned plasma production section 12, a base material 14, and an end plate 16 from the DC power supply which are not illustrated. The above-mentioned insulating ring 8 is for maintaining the electric insulation of this high voltage. The above-mentioned high voltage is usually impressed also to the gas installation tubing 18 and the gas supply section 20 which are connected with the plasma production section 12. Therefore, these are also usually in high potential.

[0006] Evacuation of the inside of the above-mentioned ion source housing 2 is carried out to a predetermined high vacuum (for example, 10-5 - 10-6Torr extent) by evacuation equipment 6 through a valve 4 for lessening loss of an ion beam 26 etc. In this example, the beam line tubing 30 which leads the above-mentioned ion beam 26 to a desired location is connected to the other end of this ion source housing 2 through the valve 28.

[0007] An example of the structure of the above-mentioned plasma production section 12 is shown in drawing 4. This plasma production section 12 is the same, and it has the plasma production container 32 with which the above-mentioned ion source gas 22 is introduced, the filament 38 of the shape of U character established in that one side, and the reflector 42 prepared in the other side of the plasma production container 32 as it was indicated by JP,9-35648,A. Between the filament 38 and the reflector 42, and the plasma production container 32, it insulates electrically with insulators 40 and 44, respectively.

[0008] The ion cash-drawer slit 34 is formed in the front section of the plasma production container 32. A field 37 is impressed in the direction in alignment with the shaft which ties a filament 38 and a reflector 42 with the field generating means which is not illustrated in the plasma production container 32.

[0009] By carrying out energization heating of the filament 38, and producing arc discharge between it and the plasma production container 32, discharge decomposition of the ion source gas 22 can be carried out, and the plasma 36 can be generated. The above-mentioned field 37 and a reflector 42 serve to raise the electrolytic dissociation efficiency of gas in that case.

[Problem(s) to be Solved by the Invention] In the above-mentioned ion source equipment, a part of ion source gas 22 introduced into the plasma production section 12 begins to leak unescapable in the ion source housing 2 through the ion cash-drawer slit 34. And the conductive dirt containing B and As which constitute this ion source gas 22, P, etc. adheres to the inside of the ion source housing 2 and insulating ring 8 grade.

[0011] When this dirt advances, it becomes impossible to impress the predetermined high voltage mentioned above in the above-mentioned plasma production section 12 grade, and it becomes impossible to operate this ion source equipment, since especially the above-mentioned dirt adhering to the inside of an insulating ring 8 wakes up the poor insulation of an insulating ring 8

[0012] In order to prevent this, sometimes the operation needed to be stopped, the equipment concerned needed to be disassembled, the insulating ring 8 needed to be cleaned, and conventional ion source equipment had taken very much time and effort and time amount. Moreover, the quiescent time of equipment became long and operation effectiveness was bad. [0013] Then, this invention sets it as the main purpose to offer the ion source equipment from which it enabled it to remove dirt, such as an inside of the above insulating rings, simply.

[Means for Solving the Problem] The ion source equipment of this invention is characterized by having the cleaning gas supply system which supplies the cleaning gas containing halogen gas in said ion source housing.

[0015] According to the above-mentioned configuration, by supplying cleaning gas in ion source housing, the dirt adhering to the inside of the above-mentioned insulating ring etc. serves as gas of a halogenide, and is removed. The gas of the removed halogenide is discharged out of ion source housing in connection with carrying out evacuation of the inside of ion source housing. Thus, compared with the case where equipment is moreover disassembled, dirt, such as an inside

of an insulating ring, can be removed very much easily in a short time, without disassembling equipment. Therefore, the operation effectiveness of equipment also improves.
[0016]

[Embodiment of the Invention] <u>Drawing 1</u> is the sectional view showing an example of the ion source equipment concerning this invention. The same sign is given to the same as that of the conventional example shown in <u>drawing 3</u>, or a corresponding part, and difference with the conventional example concerned is mainly explained below.

[0017] This ion source equipment is equipped with the cleaning gas supply system 52 which supplies the cleaning gas 58 containing halogen gas in the ion source housing 2 mentioned above.

[0018] This cleaning gas supply system 52 has the source 54 of cleaning gas and valve 56 which are prepared in the gas supply section 20 mentioned above, and supply cleaning gas 58, and the gas installation tubing 18 which supplies the cleaning gas 58 from this source 54 of cleaning gas to the plasma production section 12 in this example. In the gas supply section 20 concerned, the ion source gas supply system 46 which has the source 48 of ion source gas and valve 50 which supply the ion source gas 22 mentioned above is also established. The gas installation tubing 18 of each other is shared in this example by the ion source gas supply system 46 and the cleaning gas supply system 52. Therefore, in this example, at the time of cleaning, cleaning gas 58 is supplied via the gas installation tubing 18 in the plasma production section 12 (plasma production container 32 specifically shown in that drawing 4), and cleaning gas 58 is further supplied in the ion source housing 2 via this plasma production section 12 (ion cash-drawer slit 34 specifically shown in that drawing 4).

[0019] The above-mentioned cleaning gas 58 is the mixed gas of fluorine gas, chlorine gas, chlorine gas, halogen gas like sulfur fluoride gas or the halogen gas concerned, and other gas (for example, inert gas).

[0020] Explanation of an example of the operating method of the above-mentioned ion source equipment pulls out an ion beam 26 according to the operation which pulls out an ion beam 26 and which closed the valve 56, opened the valve 50, and supplied and mentioned ion source gas 22 above from the ion source gas supply system 46 to the plasma production section 12 while the valve 4 was opened at the time of operation and it usually carried out evacuation of the inside of the ion source housing 2 with evacuation equipment 6. The valve 28 is also opened at this time. [0021] Valves 28, 4, and 50 are closed at the time of the cleaning in the ion source housing 2, a valve 56 is opened and cleaning gas 58 is supplied in the plasma production section 12 and the ion source housing 2 from the cleaning gas supply system 52. Cleaning gas 58 is filled in the plasma production section 12 and the ion source housing 2, and the dirt by B and As adhering to the inside of an insulating ring 8 which were mentioned above, P, etc. serves as gas of a halogenide, for example, it becomes gas boron fluoride (for example, BF3), arsenic fluoride (for example, AsF3), phosphorus fluoride (for example, PF3), etc., and is removed from the inside of an insulating ring 8 by this. Therefore, the insulating engine performance of an insulating ring 8 can be recovered.

[0022] Dirt, such as B and As adhering to the insulators 40 and 44 (refer to drawing 4) mentioned above in the plasma production section 12, and P, also serves as gas of the above halogenides, and is removed from the front face of insulators 40 and 44 by coincidence. Therefore, the insulating engine performance of these insulators 40 and 44 can also be recovered. [0023] Furthermore, the above dirt adhering to the inside of the ion source housing 2 as well as the above is removed.

[0024] And if fixed time amount (for example, time amount beforehand defined by trial) passes, a valve 56 will be closed, and a valve 4 will be opened, and the inside of the ion source housing 2 will be exhausted with evacuation equipment 6. The gas of the above-mentioned halogenide is discharged out of the ion source housing 2 by this. In connection with it, the degree of vacuum in the ion source housing 2 improves.

[0025] If the degree of vacuum in the ion source housing 2 reaches a predetermined thing (to for example, 10-5 - 10-6 Torr extent), the drawer of an ion beam 26 can be resumed.

[0026] According to this ion source equipment as mentioned above, compared with the case where equipment is moreover disassembled, the dirt of the inside of an insulating ring 8, the dirt of the front face of the insulators 40 and 44 which constitute the plasma production section 12, etc. can be removed very much easily in a short time, without disassembling equipment. Therefore, the operation effectiveness of equipment also improves.

[0027] In addition, a valve 60 and the gas installation tubing 62 are formed, and you may make it supply cleaning gas 58 near the inside of an insulating ring 8 from this gas installation tubing 62 further like the example shown in <u>drawing 2</u> at the above-mentioned cleaning gas supply system 52. If it is made such, since cleaning gas 58 can be efficiently supplied to the inside of an insulating ring 8, it becomes possible to remove the dirt of the inside of an insulating ring 8 more efficiently.

[0028]

[Effect of the Invention] Since it has the above cleaning gas supply systems as mentioned above according to this invention, compared with the case where equipment is moreover disassembled, dirt, such as an inside of an insulating ring, can be removed very much easily in a short time, without disassembling equipment. Therefore, the operation effectiveness of equipment also improves.

| [Translation done.] | |
|--|------------|
| TECHNICAL FIELD | |
| [Field of the Invention] This invention is used for ion implantation equipment etc., and, more specifically, relates to a means to remove dirt, such as an inside of the above-mentioned insulating ring, simply, about the ion source equipment of the structure holding the ion source head which has the plasma production section through an insulating ring in ion source housing | , . |
| [Translation done.] | |
| PRIOR ART | |

[Description of the Prior Art] The conventional example of this kind of ion source equipment is shown in <u>drawing 3</u>. This ion source equipment is having structure holding the ion source head 10 which has the plasma production section 12 through the insulating ring 8 attached in the tubed

ion source housing 2 at that end section. The ion source head 10 has further the end plate 16 which supports the base material 14 which supports the plasma production section 12, and this base material 14 in this example. The end plate 16 is attached in the heel of an insulating ring 8. [0003] Ion source gas 22 is introduced into the plasma production section 12 via the gas installation tubing 18 from the gas supply section 20. Although the plasma production section 12 is mentioned later for details, discharge decomposition of this ion source gas 22 is carried out, and it generates the plasma 36 (refer to drawing 4). ion source gas 22—for example, BF3, AsH3, and PH3 etc.—it is gas containing dopants (impregnation impurity to a semi-conductor), such as B, As, and P, like.

[0004] It is in the ion source housing 2, and the cash-drawer electrode 24 which pulls out an ion beam 26 from the plasma generated within the plasma production section 12 is arranged near the front of the plasma production section 12, the base material which does not illustrate this cash-drawer electrode 24 -- and a required insulation is secured and it is supported from the ion source housing 2.

[0005] In order to accelerate and pull out an ion beam 26 to predetermined energy, the forward high voltage (for example, about 20-50kV) is impressed to the above-mentioned plasma production section 12, a base material 14, and an end plate 16 from the DC power supply which are not illustrated. The above-mentioned insulating ring 8 is for maintaining the electric insulation of this high voltage. The above-mentioned high voltage is usually impressed also to the gas installation tubing 18 and the gas supply section 20 which are connected with the plasma production section 12. Therefore, these are also usually in high potential.

[0006] Evacuation of the inside of the above-mentioned ion source housing 2 is carried out to a predetermined high vacuum (for example, 10-5 - 10-6Torr extent) by evacuation equipment 6 through a valve 4 for lessening loss of an ion beam 26 etc. In this example, the beam line tubing 30 which leads the above-mentioned ion beam 26 to a desired location is connected to the other end of this ion source housing 2 through the valve 28.

[0007] An example of the structure of the above-mentioned plasma production section 12 is shown in <u>drawing 4</u>. This plasma production section 12 is the same, and it has the plasma production container 32 with which the above-mentioned ion source gas 22 is introduced, the filament 38 of the shape of U character established in that one side, and the reflector 42 prepared in the other side of the plasma production container 32 as it was indicated by JP,9-35648,A. Between the filament 38 and the reflector 42, and the plasma production container 32, it insulates electrically with insulators 40 and 44, respectively.

[0008] The ion cash-drawer slit 34 is formed in the front section of the plasma production container 32. A field 37 is impressed in the direction in alignment with the shaft which ties a filament 38 and a reflector 42 with the field generating means which is not illustrated in the plasma production container 32.

[0009] By carrying out energization heating of the filament 38, and producing arc discharge between it and the plasma production container 32, discharge decomposition of the ion source gas 22 can be carried out, and the plasma 36 can be generated. The above-mentioned field 37 and a reflector 42 serve to raise the electrolytic dissociation efficiency of gas in that case.

[Translation done.]

EFFECT OF THE INVENTION

[Effect of the Invention] Since it has the above cleaning gas supply systems as mentioned above according to this invention, compared with the case where equipment is moreover disassembled, dirt, such as an inside of an insulating ring, can be removed very much easily in a short time, without disassembling equipment. Therefore, the operation effectiveness of equipment also improves.

[Translation done.]

TECHNICAL PROBLEM

[Problem(s) to be Solved by the Invention] In the above-mentioned ion source equipment, a part of ion source gas 22 introduced into the plasma production section 12 begins to leak unescapable in the ion source housing 2 through the ion cash-drawer slit 34. And the conductive dirt containing B and As which constitute this ion source gas 22, P, etc. adheres to the inside of the ion source housing 2 and insulating ring 8 grade.

[0011] When this dirt advances, it becomes impossible to impress the predetermined high voltage mentioned above in the above-mentioned plasma production section 12 grade, and it becomes impossible to operate this ion source equipment, since especially the above-mentioned dirt adhering to the inside of an insulating ring 8 wakes up the poor insulation of an insulating ring 8.

[0012] In order to prevent this, sometimes the operation needed to be stopped, the equipment concerned needed to be disassembled, the insulating ring 8 needed to be cleaned, and conventional ion source equipment had taken very much time and effort and time amount. Moreover, the quiescent time of equipment became long and operation effectiveness was bad. [0013] Then, this invention sets it as the main purpose to offer the ion source equipment from which it enabled it to remove dirt, such as an inside of the above insulating rings, simply.

[Translation done.]

MEANS

[Means for Solving the Problem] The ion source equipment of this invention is characterized by having the cleaning gas supply system which supplies the cleaning gas containing halogen gas in said ion source housing.

[0015] According to the above-mentioned configuration, by supplying cleaning gas in ion source housing, the dirt adhering to the inside of the above-mentioned insulating ring etc. serves as gas of a halogenide, and is removed. The gas of the removed halogenide is discharged out of ion source housing in connection with carrying out evacuation of the inside of ion source housing. Thus, compared with the case where equipment is moreover disassembled, dirt, such as an inside of an insulating ring, can be removed very much easily in a short time, without disassembling

equipment. Therefore, the operation effectiveness of equipment also improves. [0016]

[Embodiment of the Invention] <u>Drawing 1</u> is the sectional view showing an example of the ion source equipment concerning this invention. The same sign is given to the same as that of the conventional example shown in <u>drawing 3</u>, or a corresponding part, and difference with the conventional example concerned is mainly explained below.

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[0020] Explanation of an example of the operating method of the above-mentioned ion source equipment pulls out an ion beam 26 according to the operation which pulls out an ion beam 26 and which closed the valve 56, opened the valve 50, and supplied and mentioned ion source gas 22 above from the ion source gas supply system 46 to the plasma production section 12 while the valve 4 was opened at the time of operation and it usually carried out evacuation of the inside of the ion source housing 2 with evacuation equipment 6. The valve 28 is also opened at this time. [0021] Valves 28, 4, and 50 are closed at the time of the cleaning in the ion source housing 2, a valve 56 is opened and cleaning gas 58 is supplied in the plasma production section 12 and the ion source housing 2 from the cleaning gas supply system 52. Cleaning gas 58 is filled in the plasma production section 12 and the ion source housing 2, and the dirt by B and As adhering to the inside of an insulating ring 8 which were mentioned above, P, etc. serves as gas of a halogenide, for example, it becomes gas boron fluoride (for example, BF3), arsenic fluoride (for example, AsF3), phosphorus fluoride (for example, PF3), etc., and is removed from the inside of an insulating ring 8 by this. Therefore, the insulating engine performance of an insulating ring 8 can be recovered.

[0022] Dirt, such as B and As adhering to the insulators 40 and 44 (refer to drawing 4) mentioned above in the plasma production section 12, and P, also serves as gas of the above halogenides, and is removed from the front face of insulators 40 and 44 by coincidence. Therefore, the insulating engine performance of these insulators 40 and 44 can also be recovered. [0023] Furthermore, the above dirt adhering to the inside of the ion source housing 2 as well as the above is removed.

[0024] And if fixed time amount (for example, time amount beforehand defined by trial) passes,

a valve 56 will be closed, and a valve 4 will be opened, and the inside of the ion source housing 2 will be exhausted with evacuation equipment 6. The gas of the above-mentioned halogenide is discharged out of the ion source housing 2 by this. In connection with it, the degree of vacuum in the ion source housing 2 improves.

[0025] If the degree of vacuum in the ion source housing 2 reaches a predetermined thing (to for example, 10-5 - 10-6Torr extent), the drawer of an ion beam 26 can be resumed.

[0026] According to this ion source equipment as mentioned above, compared with the case where equipment is moreover disassembled, the dirt of the inside of an insulating ring 8, the dirt of the front face of the insulators 40 and 44 which constitute the plasma production section 12, etc. can be removed very much easily in a short time, without disassembling equipment. Therefore, the operation effectiveness of equipment also improves.

[0027] In addition, a valve 60 and the gas installation tubing 62 are formed, and you may make it supply cleaning gas 58 near the inside of an insulating ring 8 from this gas installation tubing 62 further like the example shown in <u>drawing 2</u> at the above-mentioned cleaning gas supply system 52. If it is made such, since cleaning gas 58 can be efficiently supplied to the inside of an insulating ring 8, it becomes possible to remove the dirt of the inside of an insulating ring 8 more efficiently.

[Translation done.]

DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] It is the sectional view showing an example of the ion source equipment concerning this invention.

[Drawing 2] It is the sectional view showing other examples of the ion source equipment concerning this invention.

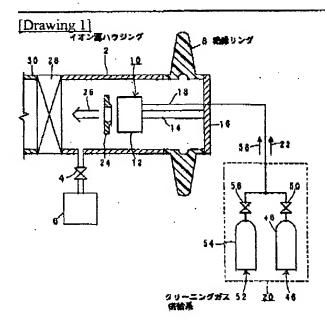
[Drawing 3] It is the sectional view showing an example of conventional ion source equipment.
[Drawing 4] It is the sectional view showing the example of a detail of the circumference of the plasma production section in <u>drawing 1</u> thru/or <u>drawing 3</u>.

[Description of Notations]

- 2 Ion Source Housing
- 6 Evacuation Equipment
- 8 Insulating Ring
- 10 Ion Source Head
- 12 Plasma Production Section
- 18 Gas Installation Tubing
- 20 Gas Supply Section
- 22 Ion Source Gas
- 46 Ion Source Gas Supply System
- 52 Cleaning Gas Supply System
- 58 Cleaning Gas

[Translation done.]

DRAWINGS



[Drawing 2]

[Drawing 3]

[Drawing 4]

[Translation done.]

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